

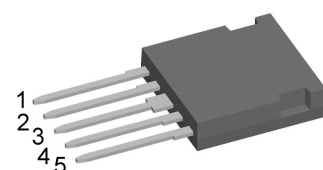
HiPerFRED

V_{RRM}	=	600 V
I_{DAV}	=	22 A
t_{rr}	=	30 ns

High Performance Fast Recovery Diode
 Low Loss and Soft Recovery
 1~ Rectifier Bridge

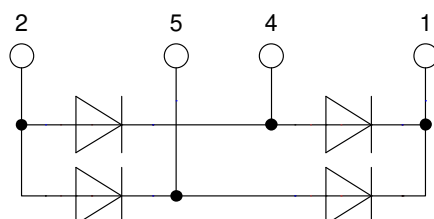
Part number

FBE22-06N1



Backside: isolated

 E72873



Features / Advantages:

- Planar passivated chips
- Very low leakage current
- Very short recovery time
- Improved thermal behaviour
- Very low I_{rm} -values
- Very soft recovery behaviour
- Avalanche voltage rated for reliable operation
- Soft reverse recovery for low EMI/RFI
- Low I_{rm} reduces:
 - Power dissipation within the diode
 - Turn-on loss in the commutating switch

Applications:

- Rectifiers in switch mode power supplies (SMPS)

Package: i4-Pac

- Isolation Voltage: 3000 V~
- Industry convenient outline
- RoHS compliant
- Epoxy meets UL 94V-0
- Soldering pins for PCB mounting
- Backside: DCB ceramic
- Reduced weight
- Advanced power cycling

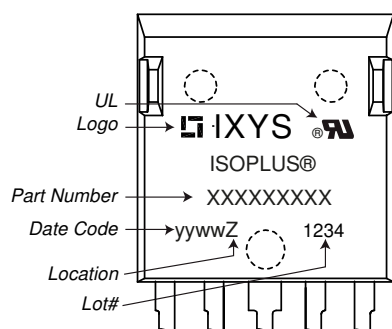
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Fast Diode				Ratings				
Symbol	Definition	Conditions		min.	typ.	max.	Unit	
V _{RSM}	max. non-repetitive reverse blocking voltage	T _{VJ} = 25°C				600	V	
V _{RRM}	max. repetitive reverse blocking voltage	T _{VJ} = 25°C				600	V	
I _R	reverse current, drain current	V _R = 600 V	T _{VJ} = 25°C			60	μA	
		V _R = 600 V	T _{VJ} = 150°C			0.25	mA	
V _F	forward voltage drop	I _F = 11 A	T _{VJ} = 25°C			2.13	V	
		I _F = 22 A				2.35	V	
		I _F = 11 A	T _{VJ} = 150°C			1.44	V	
		I _F = 22 A				1.71	V	
I _{DAV}	bridge output current	T _C = 115°C rectangular d = 0.5	T _{VJ} = 175°C			22	A	
V _{F0}	threshold voltage	} for power loss calculation only		T _{VJ} = 175°C		1.04	V	
r _F	slope resistance					24	mΩ	
R _{thJC}	thermal resistance junction to case					3	K/W	
R _{thCH}	thermal resistance case to heatsink				0.2		K/W	
P _{tot}	total power dissipation	T _C = 25°C				50	W	
I _{FSM}	max. forward surge current	t = 10 ms; (50 Hz), sine; V _R = 0 V		T _{VJ} = 45°C		50	A	
C _J	junction capacitance	V _R = 400 V f = 1 MHz		T _{VJ} = 25°C	6		pF	
I _{RM}	max. reverse recovery current	} I _F = 10 A; V _R = 300 V -di _F /dt = 200 A/μs		T _{VJ} = 25 °C	3.5		A	
				T _{VJ} = 100 °C	6		A	
t _{rr}	reverse recovery time			T _{VJ} = 25 °C	30		ns	
				T _{VJ} = 100 °C	90		ns	

Package i4-Pac			Ratings			
Symbol	Definition	Conditions	min.	typ.	max.	Unit
I_{RMS}	RMS current	per terminal			35	A
T_{VJ}	virtual junction temperature		-55		175	°C
T_{op}	operation temperature		-55		150	°C
T_{stg}	storage temperature		-55		150	°C
Weight				9		g
F_c	mounting force with clip		20		120	N
$d_{Spp/App}$	creepage distance on surface / striking distance through air	terminal to terminal	1.7			mm
$d_{Spb/Apb}$		terminal to backside	5.1			mm
V_{ISOL}	isolation voltage	t = 1 second	3000			V
		t = 1 minute	2500			V

Product Marking

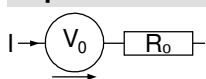


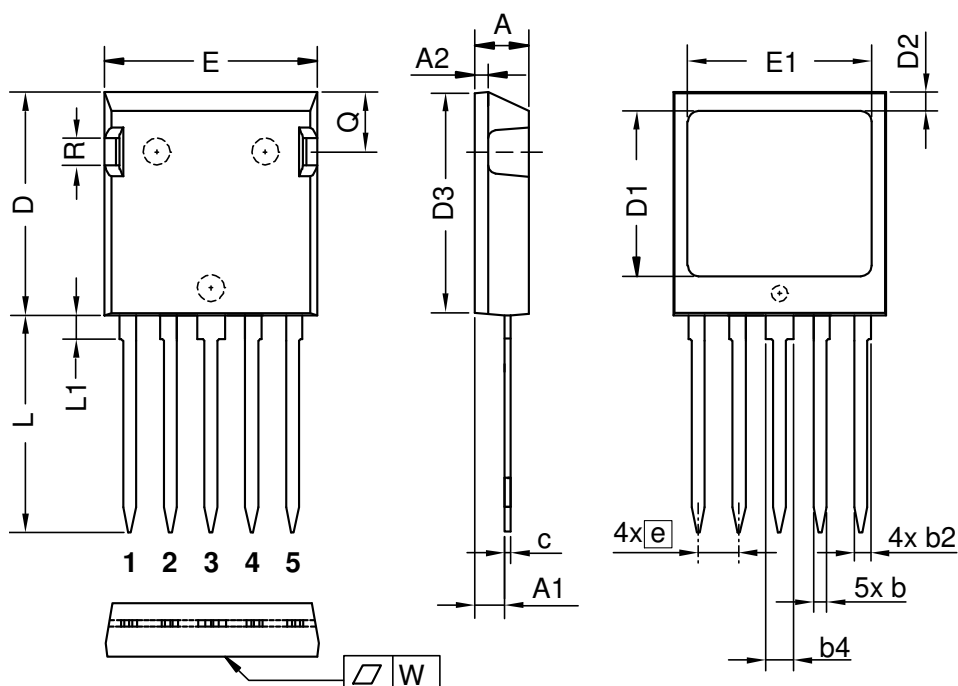
Ordering	Ordering Number	Marking on Product	Delivery Mode	Quantity	Code No.
Standard	FBE22-06N1	FBE22-06N1	Tube	25	484954

Equivalent Circuits for Simulation

* on die level

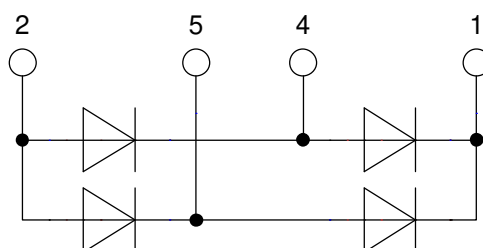
$T_{VJ} = 175^{\circ}\text{C}$

			Fast Diode	
$V_{0\max}$	threshold voltage	1.04		V
$R_{0\max}$	slope resistance *	21		mΩ

Outlines i4-Pac


Dim.	Millimeter		Inches	
	min	max	min	max
A	4.83	5.21	0.190	0.205
A1	2.59	3.00	0.102	0.118
A2	1.17	2.16	0.046	0.085
b	1.14	1.40	0.045	0.055
b2	1.47	1.73	0.058	0.068
b4	2.54	2.79	0.100	0.110
c	0.51	0.74	0.020	0.029
D	20.80	21.34	0.819	0.840
D1	14.99	15.75	0.590	0.620
D2	1.65	2.03	0.065	0.080
D3	20.30	20.70	0.799	0.815
E	19.56	20.29	0.770	0.799
E1	16.76	17.53	0.660	0.690
e	3.81 BSC		0.150 BSC	
L	19.81	21.34	0.780	0.840
L1	2.11	2.59	0.083	0.102
Q	5.33	6.20	0.210	0.244
R	2.54	4.57	0.100	0.180
W	-	0.10	-	0.004

Die konvexe Form des Substrates ist typ. < 0.05 mm über der Kunststoffoberfläche der Bauteilunterseite
 The convexbow of substrate is typ. < 0.05 mm over plastic surface level of device bottom side



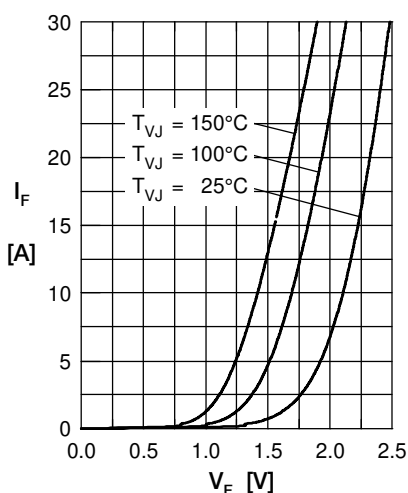
Fast Diode


Fig. 1 Forward current
 I_F versus V_F

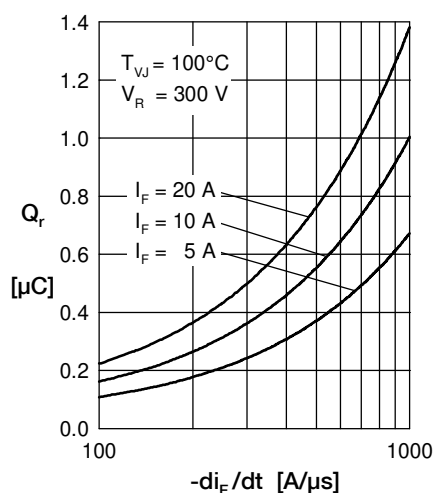


Fig. 2 Typ. reverse recov. charge
 Q_r versus $-di_F/dt$

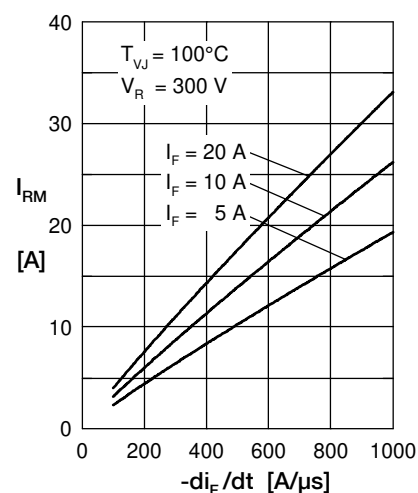


Fig. 3 Typ. peak reverse current
 I_{RM} versus $-di_F/dt$

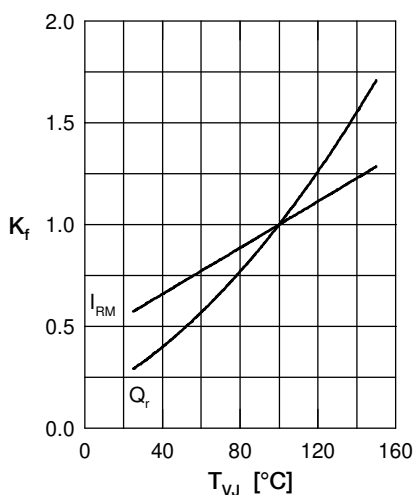


Fig. 4 Dynamic parameters
 Q_r , I_{RM} versus T_{VJ}

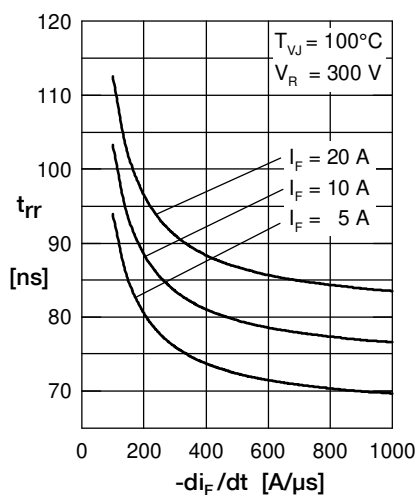


Fig. 5 Typ. recovery time
 t_{rr} versus $-di_F/dt$

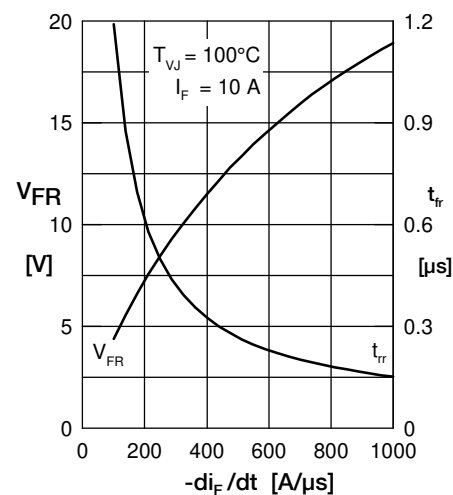


Fig. 6 Typ. peak forward voltage
 V_{FR} and t_{rr} versus di_F/dt

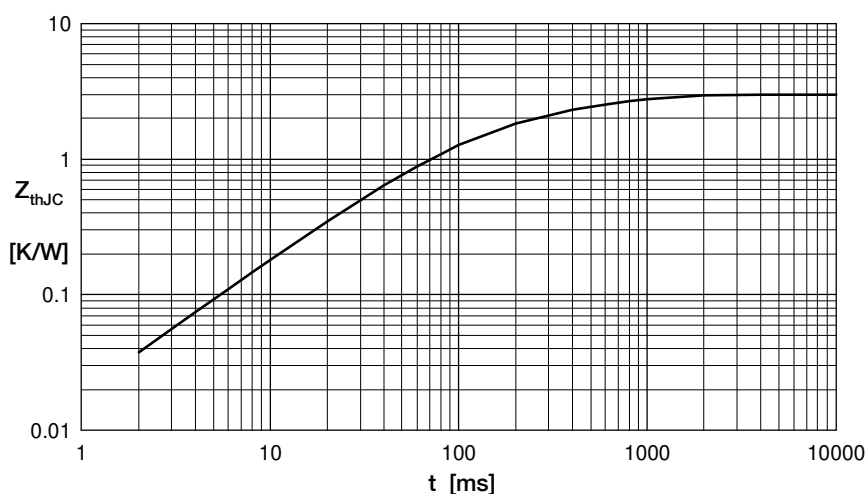


Fig. 7 Transient thermal impedance junction to case

Constants for Z_{thJC} calculation:

i	R_{thi} [K/W]	t_i [s]
1	1.3590	0.1015
2	0.4651	0.1026
3	0.8473	0.4919
4	0.8473	0.6200